Reaction layer dynamics in ion-assisted Si/XeF2 etching: temperature dependence

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I. INTRODUCTION

Etching is one of the important steps in the production of semiconductor devices. The characteristics of the etching process are largely determined by the reaction layer formed on the surface. It can be defined as the surface layer consisting of intermediate reaction products and residues of the etchant. The reaction layer can influence all steps of the etching process: etchant adsorption, reaction product formation, and release of reaction products. The role of the reaction layer depends on the specific etching process. In the case of Si etching with CF₄ gases, the reaction layer limits the supply of reactants (step 1). When Si is etched by XeF₂, Vugts et al. showed that it is the reaction layer’s fluorine content which determines the spontaneous etch rate (step 2). Finally, the condensation of SiF₂ at 77 K blocks the etching process is an example of a case in which the reaction layer limits the release of reaction products (step 3).

Etching of Si by XeF₂ and Ar⁺ is often used as a model system to study the fundamental mechanisms behind etching. However, despite its importance, little attention has been paid to the role of the reaction layer, particularly in the case of ion-assisted etching. In this article we study the dynamics of the reaction layer during spontaneous etching (i.e., without ions) at ordinary temperatures can be summarized by the following steps:

(i) Physisorption of XeF₂ in a precursor state.
(ii) Chemisorption of the precursors. On a clean surface, chemisorption first takes place at dangling bonds. Next, a SiF₂-like monolayer coverage is formed which changes into a multilayer coverage with SiₓFᵧ chains on longer time scales.

(iii) Desorption of chemisorbed surface species (SiF₂).
(iv) Formation of volatile reaction products (SiF₄), when physisorbed XeF₂ reacts with surface species.

The first two steps contribute to the formation of the reaction layer while the last two steps remove surface species. A steady-state reaction layer is formed when there is a balance between steps (i) and (ii) on one side and steps (iii) and (iv) on the other side. In the presence of ions, steps (iii) and (iv) are enhanced, which results in a shift of the balance. As a function of the ion flux, this was discussed in a previous article.

Temperature also influences the formation of the reaction layer and will shift the equilibrium. In the case of spontaneous etching the dynamics of the reaction layer as a function of temperature were studied by Vugts et al.

In this article we study the dynamics of the reaction layer during ion-assisted etching in the temperature range 150–800 K. The measurements were done with an ion-to-neutral flux ratio R = 0.025. For this flux ratio, it was concluded that the adsorption of fluorine on dangling bonds created by the ions plays an important role at room temperature. The total reaction probability for this flux ratio is ε = 0.72, which is near the maximum reaction probability of ε = 0.88 in the limit of high flux ratios.

This article is organized as follows. After a brief description of the experimental setup in Sec. II, the dynamics of the reaction layer on a time scale of 100 s will be discussed in Sec. III. On this time scale, given a neutral flux of 0.55 ML/s, the reaction layer created during spontaneous etching is removed when the ions are switched on and a new steady-state situation is reached. When the ions are switched off again after 180 s, the reaction layer will reconstruct to the...
initial situation of spontaneous etching. This process is studied by looking at the response of the SiF₄ production, since this reaction product is formed within the reaction layer and thus gives information about the reaction layer. All experimental evidence leads to the conclusion that, independent of temperature, a reaction layer with a submonolayer fluorine coverage is formed in steady-state ion-assisted etching.

Based on this conclusion, a model is presented in Sec. IV to describe the steady-state values of the reaction probability of XeF₂, as a function of both temperature and ion flux. This model gives a good description of the reaction probability and indicates that the precursor concentration decreases under ion bombardment, especially at low temperatures.

In Sec. VI, the behavior of the precursor layer is studied by short-pulse measurements on a time scale of seconds. These pulse measurements confirm the model and also show that SiF₄ is formed by the same mechanisms over the whole temperature range. Finally, the conclusions are summarized in Sec. VII.

II. EXPERIMENTAL SETUP

Only the basic features of the experimental setup are described here. More details are given in a previous article.¹² The Si(100) sample (n type, 30–70 Ω cm) is placed at the intersection of the XeF₂ and Ar⁺ beams in an ultrahigh vacuum (UHV) chamber (5×10⁻⁸ mbar). The sample is mounted on a nickel sample holder which is heated by means of a coaxial heating wire and cooled by a liquid nitrogen vessel. The temperature of the sample is measured by a thermocouple which is placed 1 mm behind the sample in the sample holder. In the experiments a XeF₂ flux Φₓ(XeF₂) = 0.55 ML/s and an ion flux Φₓ(Ar⁺) = 0.014 ML/s were used. This corresponds to an ion-to-neutral flux ratio R = 0.025. From previous measurements it is concluded that for such low flux ratios, the etch rate is already limited by the neutral flux. During the experiments several Si samples, which were cleaned by HF to remove native oxide, were used.

The etching reaction is monitored by a quadrupole mass spectrometer (QMS) positioned along the surface normal of the sample in a separate UHV chamber (1×10⁻⁸ mbar). The geometry of the flow resistances ensures that 85% of the mass spectrometer signal consists of species that reach the mass spectrometer directly from the sample without any wall collisions. To measure the XeF₂ flux we used the XeF⁺ signal since this is the largest signal.

The reaction probability ε of the XeF₂ gas is measured by comparing the XeF₂ flux Φₓ(XeF₂) from the Si sample to the flux Φₓ(XeF₂) diffusively scattered from an inert nickel reference plate

\[ ε = \frac{Φₓ(XeF₂) - Φₓ(XeF₂)}{Φₓ(XeF₂)} \]  

(1)

The SiF₄ signal is presented in terms of the production coefficient δ₄, defined as the probability of an incoming fluorine atom to form SiF₄, as given by

\[ δ₄ = \frac{4Φ(SiF₄)}{2Φₓ(XeF₂)} \]  

(2)

The production coefficient δ₄ is calibrated from a fluorine mass balance during spontaneous etching in steady state at room temperature when SiF₄ is the only reaction product, hence

\[ ε₀ = δ₄,₀. \]  

(3)

Here, the subscript “₀” indicates the steady-state values during spontaneous etching. For the steady-state values during ion-assisted etching, we use the subscript “ion.”

To include the temperature-dependent detection probabilities of the QMS, all measured mass spectrometer signals I(T) (both the XeF⁺ and SiF₄) are corrected to I_corr, given by

\[ I_{corr} = I(T) \left( 0.15 + 0.85 \sqrt{\frac{T_{room}}{T}} \right) \]  

(4)

Here it is assumed that 85% of the signal consists of species directly leaving the surface with a velocity distribution corresponding to the surface temperature T, while the other 15% consists of species which reach the mass spectrometer after at least one wall collision and thus have a velocity distribution corresponding to the wall temperature T = T_room. For the XeF₂ signal scattered from the nickel, a different calibration curve is used, because at high temperatures nickel cannot be considered to be inert to XeF₂.

Ion pulses are created by switching the acceleration voltage of the ion gun with a relay. The response time of this system is 24.8±0.1 ms for 2.5 keV ions, much faster than the time scale of our measurements. In the long ion pulses, the ion beam is switched manually and the mass spectrometer signals are averaged for one second. For the short-pulse measurements, the SiF₄ and XeF₂ signals are measured with a multiscaler which has 256 channels and user-defined channel times. While counting, the multiscaler also produces user-defined pulses (5 V) to switch the ion beam. In the short-pulse experiments, channel times of 50 ms have been used and the ion beam was switched on for 75 channels and switched off for 175 channels. Before each short-pulse experiment it is ensured that a steady-state reaction layer during spontaneous etching is formed. Then the ion beam is switched on for about 120 s so a steady-state situation during ion-assisted etching is reached. Then, the response of the SiF₂ and XeF₂ signal is measured for 15 subsequent ion pulses.

III. LONG-PULSE MEASUREMENTS

A typical response of the production coefficient δ₄ to an ion pulse of 180 s at room temperature is shown in Fig. 1. In this figure, the parameters used to characterize the SiF₄ response as a function of the temperature are indicated. When the ions are switched on, a peak in SiF₄ production is observed. From the area under this transient peak, the amount of fluorine L_upper released from the reaction layer can be calculated. After the transient peak, a steady-state value δ₄,ion is
Finally, when the ions are switched off, the production coefficient $\delta_4$ drops below the spontaneous value $\delta_{4,0}$ and reaches a minimum value $\delta_{4,min}$ after some time. On a time scale of 1000 s the steady-state value $\delta_{4,0}$ is recovered. Because of the influence of surface roughness on the etching process as a function of temperature, these parameters will only be discussed qualitatively as a function of temperature.

### A. Steady-state values

The steady-state values $\epsilon_0$, $\epsilon_{ion}$, and $\delta_{4,ion}$ for the measured flux ratio $R = 0.025$ are plotted in Fig. 2 as a function of the temperature. We see that the spontaneous $\text{SiF}_4$ production $\delta_{4,0} = \epsilon_0$ increases with decreasing temperature from $\delta_{4,0} = 0.15$ at room temperature to $\delta_{4,0} = 0.95$ at 150 K. From a comparison of $\delta_{4,0}$ with $\delta_{4,ion}$ we see that the steady-state $\text{SiF}_4$ production is enhanced by the ions, while for lower temperatures it is decreased by the ions. It is also seen that $\delta_{4,ion}$ increases slightly with decreasing temperature. In contrast to the production coefficient $\delta_{4,ion}$, the reaction probability $\epsilon_{ion}$ always increases under ion bombardment. The difference $\epsilon_{ion} - \delta_{4,ion}$ is due to $\text{SiF}_4$ production.\(^\text{13}\)

The steady-state values during spontaneous and ion-assisted etching show the same trend as reported by Vugts et al.\(^\text{13}\) In the present study higher values of $\delta_{4,ion}$ and $\epsilon_{ion}$ are measured as compared to the results of Vugts et al. because of the higher ion-to-neutral flux ratio by a factor of 2 ($R = 0.025$ vs $R = 0.012$). For a detailed discussion of the steady-state values as a function of temperature, refer to Ref. 13. In this section we focus on the dynamics of the reaction layer.

### B. Transient response

In Figs. 3 and 4 the response of the production coefficient $\delta_4$ to an ion pulse of 180 s is shown at temperatures in the range $T = 150–260$ K and $T = 260–800$ K, respectively. Before the ions are switched on, it is ensured that steady-state spontaneous etching has been reached.

**Fig. 3.** Response of the $\text{SiF}_4$ production coefficient $\delta_4$ to an ion pulse of 180 s for $T < 300$ K. For $T < 210$ K, the production coefficient $\delta_4$ drops when the ions are switched on. The dashed lines indicate spontaneous $\text{SiF}_4$ production $\delta_{4,0}$ for each temperature. The steady-state value $\delta_{4,ion}$ during the ion bombardment can be found in Fig. 2.
When the ions are switched on, a transient peak in the SiF₄ production is observed over the temperature range 260–800 K (Fig. 4). From the area under the peak, it is found that the amount of fluorine $L_{\text{ion}}$ released from the reaction layer decreases at both higher and lower temperatures, as compared to room temperature.

When the ions are switched off, $\delta_i$ first drops and at $T < 600$ K it reaches a value $\delta_{i,0}$ which is lower than the spontaneous value $\delta_{i,0}$. In the temperature range $260 < T < 600$ K the value $\delta_{i,0}$ increases at higher temperatures (Fig. 4). Above 600 K no dip in SiF₄ production is observed when the ions are switched off: $\delta_{i,0} = \delta_{i,0}$.

At room temperature, the spontaneous value $\delta_{i,0}$ is reached on a time scale of 1000 s after the dip. In Fig. 3, it is seen that at lower temperatures the SiF₄ signal reaches $\delta_{i,0}$ on a shorter time scale. However, after having reached the spontaneous value $\delta_{i,0}$ at $T < 210$ K, the SiF₄ signal reaches a maximum after about 600 s after which it drops to reach $\delta_{i,0}$ again. At temperatures above room temperature the steady-state value is also reached on a shorter time scale as compared to room temperature.

The response of $\epsilon$ (not shown) shows no transient peak when the ions are switched on but increases monotonically until the steady-state value $\epsilon_{\text{ion}}$ is reached. When the ions are switched off, $\epsilon$ decreases on the time scale of seconds. After this fast decrease, $\epsilon$ reaches the same value as $\delta_i$ and shows an identical response as $\delta_i$ for the whole temperature range, including the dip.

### C. Spontaneous SiF₄ formation

To obtain a better understanding of the spontaneous SiF₄ formation, first the steps for SiF₄ formation are discussed in some more detail. With this information the experimental results can be better understood. For the precursor concentration $[XeF₂]_p$ in step $i$ in the formation of a reaction layer, Sec. I, it is assumed that it is proportional to the incoming XeF₂ flux.\(^{14}\)

$$[XeF₂]_p = c\Phi_s(XeF₂).$$

At lower temperatures a larger precursor concentration is formed during spontaneous etching\(^{11,13}\) and thus $c$ increases at decreasing temperatures.

At room temperature, the reaction layer consists of SiF–SiF₂–SiF₃ chains.\(^{3,9}\) Gray et al. showed that under ion bombardment at room temperature the reaction layer consists of SiF₂ species.\(^6\) Bermudez showed that at room temperature the reaction layer consists of SiF, SiF₂, and SiF₃ species and less fluorinated species become more important at higher temperature up to 550 K.\(^{15}\) For the purpose of modeling we assume that the reaction layer consists of only SiF₂ species, independent of ion flux and temperature.\(^{14}\)

The spontaneous SiF₄ formation and thus the desorbing flux $\Phi_{\text{spon}}(\text{SiF}_4)$ is now proportional to the precursor concentration $[XeF₂]_p$ and the SiF₂ concentration $[\text{SiF}_2]$ with a reaction probability $k_e$,

$$\Phi_{\text{spon}}(\text{SiF}_4) = k_e[\text{SiF}_2][XeF₂]_p = k_e c[\text{SiF}_2]\Phi_s(XeF₂),$$

where $k_e c$ is the overall reaction probability (physisorption followed by chemisorption) of XeF₂ to form SiF₄ spontaneously.

The SiF₂ surface species can also leave the surface and contribute to etching when their thermal energy overcomes the desorption energy of 260 meV. This process is only of importance for temperatures above 600 K.\(^{11,16}\)

### D. Discussion of transient response

During the transient peak after the ions are switched on an amount $L_{\text{ion}}$ of fluorine is observed to be released from the surface. The interpretation is that the chainlike reaction layer formed during spontaneous etching is removed (Fig. 1).\(^{10}\) The SiF₂ surface concentration decreases and a reaction layer with a submonolayer fluorine coverage is formed. The lower fluorine content of this depleted layer results in a lower spontaneous SiF₄ production [Eq. (6)], which is reflected in the dip $\delta_{i,0}$. After the dip, the chainlike reaction layer has to be rebuilt. This is a slow process,\(^{13}\) which takes over 1000 s to reach the steady-state spontaneous etch rate again. Thus, the dip and the transient peak are related: a smaller peak indicates less removal of the reaction layer, which results in a smaller dip in the SiF₄ production when the ions are switched off again.\(^{10}\)

From the behavior of the transient peak as a function of temperature (Figs. 3 and 4), it is concluded that less fluorine is removed from the reaction layer by the ions (decrease of $L_{\text{ion}}$), both at increasing and decreasing temperatures with respect to room temperature. Above room temperature this is confirmed by a smaller dip in the SiF₄ production (Fig. 4). Below room temperature, the dip cannot be measured.
correctly because the SiF₄ signal increases again on a shorter time scale and coincides with the dip. This increase in SiF₄ signal is explained by a faster reconstruction of the precursor concentration at lower temperatures which occurs on a much shorter time scale than the rebuilding of a reaction layer. The lower SiF₄ production under ion bombardment is explained by a lower precursor concentration [Eq. (6)]. Thus, besides the reaction layer, also the precursor concentration is removed by ion bombardment.

E. Comparison to thermal desorption measurements of spontaneous etching

When we compare the conclusions about the removal of the reaction layer by the ions to the results of a study of the spontaneous reaction layer by thermal desorption (TDS), similar trends are observed. In TDS measurements, the reaction layer during spontaneous etching formed at a surface temperature T is studied by the SiF₄ flux desorbing from the sample when the sample is heated after the XeF₂ flux has been turned off. As a function of the heating temperature Tₚheat several characteristics of the reaction layer are observed. First, the removal of a precursor layer is observed as the so-called “γ peak” at around Tₚheat = 200 K. The desorption of weakly-bound species is measured in an “α peak” in the temperature range of Tₚheat = 300–600 K. We interpret this peak as the desorption of species from the chainlike reaction layer. At Tₚheat = 600 K the α peak stops abruptly. Finally, the desorption of tightly bound species is measured in a “β peak” in the range of Tₚheat = 600–900 K. This corresponds to the desorption of fluorine from a reaction layer with a monolayer coverage.

Above a sample temperature of 600 K, no dip in spontaneous SiF₄ production was observed in our long-pulse measurements (Fig. 4). In the TDS measurements only a β peak is observed when the sample is heated, corresponding to a monolayer fluorine coverage during spontaneous etching. When the ions are switched on, still some release of fluorine was observed which corresponds to the creation of dangling bonds. We conclude that above sample temperatures of 600 K the reaction layer during ion-assisted etching consists of a submonolayer fluorine coverage. When the ions are switched off, the dangling bonds are fluorinated again: only a thin reaction layer has to be rebuilt and thus the SiF₂ concentration reaches steady state on a short time scale and no dip in the SiF₄ formation is observed. Because of spontaneous SiF₂ release at Tₚ> 600 K, no chainlike structures can be formed on the surface.

In the sample temperature range 250–600 K, the dip decreases at higher temperatures, which corresponds to the removal of a thinner chainlike reaction layer. From TDS measurements it is concluded that the chainlike reaction layer has a maximum fluorine content around room temperature. Thus, the fluorine removed by the ion bombardment shows the same trend as observed by TDS measurements. We already know that the reaction layer during ion-assisted etching consists of a submonolayer fluorine coverage and dangling bonds. The correspondence between the TDS measurements and the long pulse measurements now indicates that a reaction layer with a similar structure is formed in the temperature range 250–600 K.

Finally, at sample temperatures below 250 K, it is concluded from our long pulse measurements that the amount of fluorine released from the reaction layer decreases at lower temperatures. The TDS measurements show that the fluorine content of the SiF₂ chains decreases and a reaction layer with a monolayer coverage during spontaneous etching is formed at lower temperatures. No multilayer coverage can be formed at these low temperatures because of the large SiF₄ production. During spontaneous etching, the thick reaction layer is replaced by a thick precursor concentration, as observed in a γ peak in the TDS measurements.

From this, we conclude that the reaction layer below room temperature also consists of a submonolayer fluorine coverage under ion bombardment.

F. Temperature-independent reaction layer

For the ion-to-neutral flux ratio R = 0.025 it was concluded that a reaction layer with a submonolayer fluorine coverage and dangling bonds is formed during ion-assisted etching at room temperature. From a comparison between TDS measurements and the response of the SiF₄ signal upon ion bombardment, we now propose that, independent of temperature, such a reaction layer is formed. This suggests that dangling bonds are mainly created by ion impact. From previous measurements it was concluded that besides the reaction layer also the precursor layer is removed by ion bombardment. Thus, in contrast to the reaction layer, the precursor concentration is a function of both temperature and ion flux.

IV. MODEL FOR REACTION PROBABILITY

In this section a model will be presented to describe the temperature dependence of ion-assisted etching based on the suggestions from the previous sections that:

1. independent of temperature a reaction layer with a submonolayer coverage of SiF₂ and dangling bonds is formed during ion bombardment; and
2. the precursor concentration depends both on the ion flux and the temperature.

Before the model is presented, first the steady-state reaction probability at room temperature is discussed.

A. Steady-state reaction probability

At room temperature the steady-state reaction probability \( \varepsilon_0 \) during spontaneous etching is limited by the reaction probability \( k_e \) to form SiF₄ [Eqs. (2), (3), and (6)]

\[
\varepsilon_0 = 2ck_e = 0.15.
\]

Here, a totally fluorinated surface ([SiF₂] = 1) is assumed. During ion-assisted etching, \( \varepsilon_{ion} \) is limited by the much higher reaction probability \( k_f \) to fluorinate dangling bonds...
The reaction constant $k$ for the incoming XeF$_2$ flux is used to describe the precursor concentration $[\text{XeF}_2]_p$. The precursor concentration increases due to the incoming XeF$_2$ flux $\Phi_e(\text{XeF}_2)$ and decreases due to desorption and chemisorption onto dangling bonds. The reaction layer on the silicon is represented by a surface consisting of fluorinated sites and dangling bonds.

\[
\epsilon_{\text{ion}} = k_e \left( 1 + \frac{\mathcal{P}}{1 + \mathcal{P}} \right) = c k \approx 0.88,
\]  

with $\mathcal{P} = p_e/p_p$ the ratio of the probabilities for chemical and physical sputtering for the ion-induced formation of SiF$_4$ and SiF$_2$, respectively. The reaction constant $k$ can be considered as the effective reaction probability to fluorinate dangling bonds, which includes the ion-induced reaction of XeF$_2$ with fluorinated sites which results in the enhanced SiF$_4$ formation.

In Eqs. (7) and (8) it is assumed that $c$ is independent of the ion flux. The precursor concentration $c$ is already known as a function of temperature in the case of spontaneous etching. However, it was shown that $c$ is a function of the ion flux. On the other hand, we have experimental evidence in this article that the reaction layer and dangling bond concentration during ion-assisted etching is independent of temperature. Thus, to capture the temperature dependence of the etching process, we describe the precursor concentration $[\text{XeF}_2]_p$ as a function of temperature and ion flux.

**B. Precursor concentration**

The precursor concentration $[\text{XeF}_2]_p$ is described by the rate equation

\[
\frac{\partial [\text{XeF}_2]_p}{\partial t} = \Phi_e(\text{XeF}_2) - \frac{[\text{XeF}_2]_p}{\tau} - k[\text{XeF}_2]_p[\text{Si}].
\]  

Similar to the reaction layer (Sec. I), the steady-state precursor concentration $[\text{XeF}_2]_p$ results from a balance between several mechanisms (Fig. 5). In more detail, the increase by the incoming XeF$_2$ flux $\Phi_e(\text{XeF}_2)$ [first term on the right-hand side of Eq. (9)] is balanced by the decrease by thermal desorption and chemisorption (second and third term on the right-hand side). Here, only precursor-mediated chemisorption of fluorine is assumed. We assume that the thermal desorption of the precursor is the only temperature dependent process, as described by the residence time $\tau$ of XeF$_2$ in the precursor state.

\[
\tau = \tau_0 \exp\left(\frac{E_d}{k_B T}\right),
\]

with $E_d = 32$ meV the desorption energy of XeF$_2$ from the precursor state.

For chemisorption [third term on the right-hand side of Eq. (9)], the effective fluorination probability $k$ of dangling bonds is included. It is assumed that the activation energy for chemisorption is much smaller than the desorption energy and thus $k$ is considered to be independent of temperature. The chemisorption on fluorinated SiF$_2$ sites is neglected. This implies that the thermal desorption is the most important loss mechanism for XeF$_2$ from the physisorbed state during spontaneous etching.

In a steady-state situation Eq. (9) results in

\[
[\text{XeF}_2]_p = \frac{\tau_0 \Phi_e(\text{XeF}_2)}{e^{\tau_0 T} + \tau_0 k[\text{Si}]},
\]

which should be compared to Eq. (5) during spontaneous etching. We thus expressed the factor $c(R,T)$ as a function of ion flux and temperature. Equation (11) is similar to the sticking probability as predicted by the standard model for precursor-mediated chemisorption. However, in these models the usual assumption is that thermal desorption is much more important than chemisorption, comparable to spontaneous etching in our case. In the case of a high dangling bond concentration, chemisorption cannot be neglected anymore.

**C. Influence of ion flux**

It is assumed that, with increasing ion flux, the Si surface changes from a totally fluorinated surface with only SiF$_2$ species $[\text{SiF}_2]=1$ ML to a surface covered with only dangling bonds with $[\text{Si}]=1$ ML. Because of Si surface-site conservation we can write

\[
[\text{Si}] + [\text{SiF}_2] = 1 \text{ ML}.
\]

The reaction probability $\epsilon$ is given by the sum of the reaction probabilities on fluorinated sites and dangling bonds

\[
\epsilon = 2k_e c(R,T)[\text{SiF}_2] + kc(R,T)[\text{Si}],
\]

with $c(R,T)$ given by Eq. (11). For spontaneous etching ($[\text{SiF}_2]=1$ ML) and ion-assisted etching in the high flux ratio limit ($[\text{Si}]=1$ ML), Eq. (13) again yields Eqs. (7) and (8), respectively.

We now can use Eq. (13) to describe the experimental results of $\epsilon$. The values $\tau_0 k_e$ and $\tau_0 k$ are fixed by two boundary conditions

\[
T = 150 \text{ K and } [\text{Si}] = 0: \quad \epsilon = \epsilon_0 = 1,
\]

\[
T = 300 \text{ K and } [\text{Si}] = 1: \quad \epsilon = \epsilon_{\text{ion}} = 0.88.
\]

The first condition corresponds to a spontaneous reaction probability of unity at 150 K and the second condition corresponds to the maximum reaction probability in the high $R$ limit at room temperature [Eq. (8)]. These boundary conditions result in $\tau_0 k = 2.1$ and $\tau_0 k_e = 0.043$. 
Before comparing the model to the experimental results, first the precursor concentration \([\text{XeF}_2]_p\) in Eq. (11) is plotted in Fig. 6 as a function of temperature for different values of the dangling bond concentration \([\text{Si}]\). It is seen that the precursor concentration decreases a factor five in the range \(T=150–800\,\text{K}\) for spontaneous etching at \([\text{Si}]=0\,\text{ML}\). When going from a dangling bond concentration \([\text{Si}]=0\) to a concentration \([\text{Si}]=0.25\), the precursor concentration drops by a factor of 2.5 at room temperature, and by more than a factor of 6 at 150 K. It is stressed that this decrease is not the result of sputtering of the precursor but results from a higher probability for \(\text{XeF}_2\) to react with the reaction layer on dangling bonds.

When these results are applied to our experiments, a higher precursor concentration must be released from the surface at lower temperatures when switching from spontaneous to ion-assisted etching than at room temperature. Of course, a larger concentration also has to rebuild when the ions are switched off again.

Now, our model can be used to describe the experimental results. The concentration \(0<[\text{Si}]<1\,\text{ML}\) of dangling bonds on the surface is the only scaling parameter of our model: it is assumed to be independent of temperature. The temperature dependence is given by the model once a value of the dangling bond concentration is chosen.

V. REACTION PROBABILITY: EXPERIMENTS VERSUS MODEL

In Fig. 7 the model is compared to the experimental results of \(\epsilon_{\text{ion}}\) for a flux ratio \(R=0.012\) (Ref. 13) and a flux ratio \(R=0.025\) (this work) as well as those for \(\epsilon_0\). For the model calculations, in addition to the limiting cases \([\text{Si}]=0\) ML and \([\text{Si}]=1\) ML, also the curves for \([\text{Si}]=0.06\) ML and \([\text{Si}]=0.24\) ML are shown, being the best fits to the experimental results for the lower and the higher flux ratio, respectively. This indicates that flux ratio’s of \(R=0.012\) and \(R=0.025\) produce dangling bond concentrations of \([\text{Si}]=0.06\) ML and \([\text{Si}]=0.24\) ML, respectively. For ion-assisted etching, we see that the model describes the measured temperature dependence very well for both flux ratios. The model fit for spontaneous etching ([Si]=0) is not so good which may be due to surface roughness. 13

Despite the good trend of our model compared to the experimental results, we still see some small deviations for ion-assisted etching at higher temperatures. At \(T>600\,\text{K}\) an increase in \(\epsilon_{\text{ion}}\) is measured (especially for \(R=0.012\)) while our model predicts a decrease. This is explained by the fact that above 600 K also spontaneous SiF\(_2\) release becomes important, which results in a new mechanism for creating dangling bonds besides the ion bombardment. Thus, the assumption that the dangling bond concentration is independent of the temperature breaks down at \(T>600\,\text{K}\) and low flux ratios. For high flux ratios (see \(R=0.025\)), the creation of dangling bonds by thermal desorption of SiF\(_2\) seems to become less important.

A. Dangling bond concentration

The value \([\text{Si}]=0.24\,\text{ML}\) for the dangling bond for the measured flux ratio of \(R=0.025\) concentration may seem very low, since at room temperature \(\epsilon_{\text{ion}}=0.7\), which is close to the maximum reaction probability for high flux ratios [Eq. (8)]. However, a second look reveals that the spontaneous contribution to the reaction probability on fluorinated sites has dropped over a factor of 3, which is caused by a lower precursor concentration and a somewhat lower SiF\(_2\) concentration [Eq. (13)]. Thus, despite the apparently low dangling
bond concentration, the reaction probability on dangling bonds is responsible for about 90% of the total reaction probability.

A good way to interpret the dangling bond concentration \( \delta_{\text{Si}} \) is to consider the residence time of SiF\(_2\) surface species. Before a reaction product (SiF\(_4\) and SiF\(_2\)) can be formed, sites have to be fluorinated first. The calculated bare and fluorinated sites concentration is an average surface coverage during the ion bombardment. During ion-assisted etching the SiF\(_2\) residence time is much shorter than during spontaneous etching. Thus, a dangling bond concentration \( \delta_{\text{Si}} = 0.24 \) ML should be interpreted such that 24% of the time the surface site has dangling bonds and the rest of the time the site is fluorinated to produce the reaction products. It is clear that a very high ion flux is needed to assure that, on the average, a surface site is never fluorinated \( \delta_{\text{Si}} < 1 \text{ ML} \). Since the ion-to-neutral flux ratio \( R \) determines the time a site is fluorinated, it is also clear that the dangling bond concentration will only be a function of this ratio. At room temperature this was shown for ion-assisted etching by Vugts et al.\(^{14}\) Thus, at second thought, a dangling bond concentration of 24% seems very reasonable for a flux ratio \( R = 0.025 \).

**B. SiF\(_4\) production**

We can also use the model to calculate the SiF\(_4\) production. Let us assume that the SiF\(_4\) contribution to the total reaction product formation is independent of temperature. At room temperature this contribution of \( \delta_{\text{Si}} \) is 40%. In Fig. 2, the model curve \( \delta_{\text{Si}}(t) = 0.4 e^{-t} \) is plotted for our measurements at a flux ratio \( R = 0.025 \). It is seen that at \( T < 600 \) K the SiF\(_2\) production is described very well with this simple assumption.

**VI. SHORT-PULSE MEASUREMENTS**

In Sec. III it was shown that the precursor concentration is reconstructed on a much shorter time scale than the reaction layer. Therefore, the dynamics of the precursor concentration should be studied using short ion pulses. The response of \( e \) and \( \delta_{\text{Si}} \) is now studied as a function of temperature on a time scale of seconds by using ion pulses having a duration of 3.75 s and a time between subsequent pulses of 8.75 s. These measurements also serve as a validation for the model, in which the precursor concentration was described both as a function of ion flux and temperature. This model shows that at lower temperatures a higher precursor concentration has to be rebuilt after the ion bombardment has ceased (Fig. 6).

From these measurements, also conclusions can be drawn about the mechanisms for SiF\(_4\) production during ion-assisted etching as a function of temperature.\(^{10}\)

In Fig. 8 a typical response of \( e \) and \( \delta_{\text{Si}} \) at room temperature is shown. When the ions are switched on, a transient peak in SiF\(_4\) production is measured, similar to the response to pulses of 180 s (Fig. 1). This peak, however, decays on a time scale of seconds. Here, the interpretation is that fluorine is released and dangling bonds are created: the reaction layer changes from a monolayer fluorine coverage to a submonolayer fluorine coverage. When the ions are switched off, first a fast decrease in SiF\(_4\) production is observed, followed by a slower decay to \( \delta_{\text{Si,min}} \). These responses reflect two mechanisms which enhance the SiF\(_4\) production on a depleted reaction layer during ion-assisted etching. The fast decay reflects the formation of SiF\(_4\) within the reaction layer, modeled as the reaction of two SiF\(_2\) surface species to form SiF\(_4\). The slow decay reflects the enhanced formation of SiF\(_4\) from physisorbed XeF\(_2\) and excited SiF\(_2\) surface spe-

![Fig. 8. Typical response of \( e \) and \( \delta_{\text{Si}} \) to a short pulse on the time scale of seconds at room temperature. The transient at ion switch-on is attributed to the creation of dangling bonds. Upon ion switch-off, a fast and a slow response are observed which are related to the formation of SiF\(_4\) within the reaction layer and from excited surface species, respectively. At ion switch-off, it is seen that \( e \) has a slower response than \( \delta_{\text{Si}} \) which is attributed to the fluorination of the dangling bonds.](image-url)
cies, which decay during the slow process to SiF₂ species with a low reaction probability.¹⁰

In the response of ε no transient peak is observed. During the increase of ε at ion switch-on, the higher reaction probability is attributed to the increasing dangling bond concentration (cf. the response of δ₁). The difference between ε and δ₁ during steady state is explained by the production of SiF₂. The response of ε at ion switch-off is much slower than the response of δ₁. This difference is explained by the fluorination of dangling bonds. The difference in the amount of fluorine that reacts with the dangling bonds during ion switch-off (from the behavior of ε) and the much smaller amount that is released in the transient peak (hatched area in Fig. 8) is explained by an additional transient peak in the SiF₂ production.

The response of δ₃ at temperatures below and above room temperature is shown in Figs. 9 and 10, respectively. On the time scale of these measurements, no steady-state situation of spontaneous etching is reached during the ion switch-off period. The corresponding steady-state values are indicated in Fig. 9. The response of ε as a function of temperature is shown in Fig. 11. In the following sections, first the temperature dependence of ion switch-off and next the transient at ion switch-on is discussed.

A. Temperature dependence of switch-off behavior

At ion switch-off, a fast decay of SiF₄ production is observed over the whole temperature range in Figs. 9 and 10. Thus the production of SiF₄ in the reaction layer is a valid ion-assisted mechanism for enhanced SiF₄ production at all temperatures.

After this initial fast decrease in δ₁, a temporary peak in δ₄ is measured for T = 200 and 230 K (Fig. 9). This temporary peak after the ion switch-off increases with decreasing temperature. It is explained by a competition of a decreasing excited SiF₂ concentration (slow decay) and an increasing precursor concentration. The broad peak in the SiF₄ production is observed because the reconstruction takes place on a shorter time scale than the decay of excited SiF₂ surface species. At 230 K, the precursor concentration is only lowered slightly by the ion bombardment and thus is recon-
structured again after a few seconds. For even lower temperatures \( T \leq 173 \) K, a higher precursor concentration has to be rebuilt, which takes longer. Here, no temporary peak is observed but the SiF\(_2\) production increases monotonically.

Above 300 K (Fig. 10), the slow response decreases at higher temperatures. Above 600 K no slow response is observed and constant SiF\(_2\) production is reached directly after the fast decay. However, above 600 K roughening plays an important role as can be concluded from the fact that \( \epsilon_d \) does not increase significantly at these temperatures (Fig. 2), in contrast to the measurements by Vugts et al.\(^{11}\) The effect of roughening on ion-assisted etching at these temperatures is not known and could result in a decrease of the slow response. For this reason we choose not to discuss this feature further.

Now, the response of the reaction probability \( \epsilon \) is discussed (Fig. 11). Similar to the response on a long time scale, \( \epsilon \) increases and decreases monotonously when the ions are switched on and off, respectively. An interesting feature is observed when the ions are switched off. Above room temperature \( \epsilon \) starts to decrease at the moment that the ions are switched off (discontinuity in first derivative). At lower temperatures, however, \( \epsilon \) decreases more slowly (continuous behavior of first derivative). At \( T = 173 \) K it is seen that \( \epsilon \) stays constant for about 2 s after the ions have been switched off before it starts to decrease, in stark contrast to the immediate response at room temperature.

This behavior of \( \epsilon \) at ion switch-off is attributed to the rebuilding of the precursor concentration. According to the model, a thicker precursor layer has to be rebuilt (Fig. 6) and thus more XeF\(_2\) will be physisorbed after ion switch-off at lower temperatures. This can be seen in the response of \( \epsilon \), since it takes longer for the reaction probability to drop at lower temperatures.

**B. Temperature dependence of switch-on behavior**

Now that the decay of the SiF\(_2\) signal upon ion switch-off has been discussed, the transient peak upon ion switch-on will be discussed. In the temperature range 300–600 K (Fig. 10) a small transient peak is observed. This is attributed to the release of fluorine when dangling bonds are created on the surface; at the time of ion switch-off these dangling bonds are fluorinated again.\(^{10}\) At lower temperatures the magnitude of this transient decreases significantly (Fig. 9). This is attributed to the removal of the precursor layer which has been reconstructed during the ion switch-off period. Thus, the excess precursors react to form SiF\(_4\). This is another indication that a thicker precursor concentration is present at lower temperatures.

**C. Conclusions from short pulses**

Summarizing, for the whole temperature range 150–800 K, the SiF\(_2\) formation on a depleted reaction layer is enhanced by the same mechanisms as identified at room temperature. Also from the response of both \( \epsilon \) and \( \delta \) we conclude that at lower temperatures a thicker precursor layer is formed. This is in agreement with our model.

From the short-pulse experiments, the decrease of SiF\(_4\) production under ion bombardment below 210 K can be understood in some more detail. The reason is that the spontaneous contribution decreases due to a lower precursor concentration. This is only partially offset by the fact that the ion bombardment enhances the SiF\(_4\) production again by the same mechanisms as at room temperature.

**VII. CONCLUSIONS**

Based on ion-pulse measurements on the time scale of 1–100 s, we conclude that the mechanisms for ion-assisted Si etching by XeF\(_2\) and Ar\(^+\) ions are independent of temperature in the range 150–800 K. During ion bombardment, a reaction layer is formed with a submonolayer fluorine coverage, which is independent of temperature. The dangling bond concentration is the key parameter to describe the reaction layer. Below 600 K the dangling bonds are created by ions only: a higher ion flux results in a higher dangling bond concentration. Above 600 K there is also a small contribution to the creation of dangling bonds from thermal desorption of SiF\(_2\) from the reaction layer. It is also concluded that the mechanisms of SiF\(_4\) formation are independent of temperature.

The temperature dependence of the XeF\(_2\) reaction probability \( \epsilon \) is now described by the transition of XeF\(_2\) from the precursor state to the reaction layer. In steady state, the incoming XeF\(_2\) flux is balanced by chemisorption to fluorinate the dangling bonds plus thermal desorption. During ion bombardment, dangling bonds are created on which XeF\(_2\) reacts with a high probability. Because of this high chemisorption probability, thermal desorption of XeF\(_2\) process is not important and thus the temperature dependence of \( \epsilon \) becomes less with increasing ion flux. During spontaneous etching, when no dangling bonds are presented in the reaction layer, the chemisorption probability is low which results in a strong temperature dependence of \( \epsilon \).

A simple model describes the observed temperature dependence of \( \epsilon \) as a function of the ion fluxes (and thus the dangling bond concentrations) very well. From this model also the precursor concentration is calculated as a function of both temperature and the dangling bond concentration.

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